

REMARKS

The Examiner considers claims 30-32, drawn to a nanostructure, classified in class 257, subclass 40, as one invention while claims 1-29, drawn to a method for manufacturing the nanostructure, classified in class 438, subclass 82 as two separate inventions. The Applicant provisionally elects claims 1-29 drawn to the method for manufacturing the nanostructure, however, the Applicant respectfully traverses the election requirement.

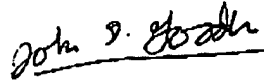
In particular, the Applicant notes that claim 31 requires "at least a portion of the residual structure has a width of less than approximately 100 nm" and claim 32 requires "at least two traces of the residual structure separated by spacing of approximately 3nm to approximately 40 nm." The Applicant submits that masking and etching without using a multi-layer organic molecule resist is not a viable alternative process and therefore this restriction should be withdrawn.

No fees or extensions of time are believed to be due in connection with this amendment; however, consider this a request for any extension inadvertently omitted, and charge any additional fees to Deposit Account No. 26-0084.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "**Version with markings to show changes made.**"

For whatever reason, should the Examiner not agree that all claims are allowable, the Examiner is respectfully invited to contact the undersigned attorney in an effort to reach mutual agreement as to the allowability of the claims. Proper reconsideration and allowance is respectfully requested.

Respectfully submitted,



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Application No. P05185US1

**AMENDMENT — VERSION WITH MARKINGS
TO SHOW CHANGES MADE**

In the Claims

Please amend claims 31 and 32 as follows:

31. The nanostructure of claim ~~29~~30 wherein at least a portion of the residual structure has a width of less than approximately 100 nm.

~~31~~32. The ~~component~~ nanostructure of claim ~~29~~31 wherein at least two traces of the residual structure are separated by a spacing of approximately 3 nm to approximately 40 nm.